

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Surface-mounted package
- Advanced trench cell design
- Super Trench
- MSL1

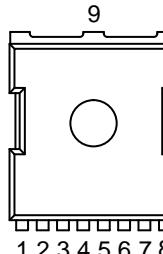
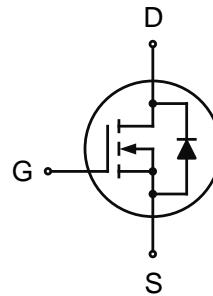
1.2 Applications

- BMS appliance
- High power inverter system
- Drones
- Light electric vehicles

1.3 Quick reference

- $BV \geq 85\text{ V}$
- $R_{DS(ON)} \leq 1.4\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 500\text{ W}$
- $I_D \leq 300\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)		
2,3,4,5,6,7,8	Source(S)		
9	Drain(D)	 Top View TOLL-8L	

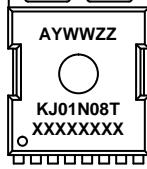
3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C = 25^\circ C$	85	-	V
V_{GS}	Gate-Source Voltage	$T_C = 25^\circ C$	-	± 20	V
I_D	Drain Current (DC)	$T_C = 25^\circ C, V_{GS} = 10 V$	-	300	A
I_D	Drain Current (DC)	$T_C = 100^\circ C, V_{GS} = 10 V$	-	267	A
I_{DM}^*	Drain Current (Pulsed)	$T_C = 25^\circ C, V_{GS} = 10 V$	-	1200	A
P_{tot}	Drain Power Dissipation	$T_C = 25^\circ C$	-	500	W
T_{stg}	Storage Temperature		-55	150	$^\circ C$
T_J	Junction Temperature		-	150	$^\circ C$
I_S	Continuous-Source Current	$T_C = 25^\circ C$	-	300	A
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD} = 40 V, L = 0.5 mH$	-	2800	mJ
$R_{\theta JA}^{**}$	Thermal Resistance-Junction to Ambient		-	32.8	$^\circ C/W$
$R_{\theta JC}^{**}$	Thermal Resistance-Junction to Case		-	0.45	$^\circ C/W$

Notes:

- * Pulse width $\leq 300 \mu s$, duty cycle $\leq 2 \%$
- ** Surface Mounted on minimum footprint pad area
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ01N08T	

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ01N08T	TOLL-8L	-	-	2000	

Note: KUAIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

6. Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}} = 0 \text{ V}, \text{I}_{\text{DS}} = 250 \mu\text{A}$	85	95	-	V
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}, \text{I}_{\text{DS}} = 250 \mu\text{A}$	2	-	4	V
I_{DSS}	Drain Leakage Current	$\text{V}_{\text{DS}} = 80 \text{ V}, \text{V}_{\text{GS}} = 0 \text{ V}$	-	-	1	μA
I_{GSS}	Gate Leakage Current	$\text{V}_{\text{GS}} = 0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA
$\text{R}_{\text{DS(ON)}}^{\text{a}}$	On-State Resistance	$\text{V}_{\text{GS}} = 10 \text{ V}, \text{I}_{\text{DS}} = 50 \text{ A}$	-	1.2	1.4	$\text{m}\Omega$
Diode Characteristics						
$\text{V}_{\text{SD}}^{\text{a}}$	Diode Forward Voltage	$\text{I}_{\text{SD}} = 50 \text{ A}, \text{V}_{\text{GS}} = 0 \text{ V}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$\text{I}_{\text{DS}} = 50 \text{ A}, \text{V}_{\text{GS}} = 0 \text{ V}$	-	120	-	nS
Q_{rr}	Reverse Recovery Charge	$\text{dI}_{\text{SD}}/\text{dt} = 100 \text{ A}/\mu\text{s}$	-	360	-	nC
Dynamic Characteristics ^b						
C_{iss}	Input Capacitance	$\text{V}_{\text{GS}} = 0 \text{ V}, \text{V}_{\text{DS}} = 50 \text{ V}$ Frequency = 1 MHz	-	14490	-	pF
C_{oss}	Output Capacitance		-	2350	-	
C_{rss}	Reverse Transfer Capacitance		-	472	-	
$\text{t}_{\text{d(on)}}$	Turn-on Delay Time	$\text{V}_{\text{DS}} = 50 \text{ V}, \text{V}_{\text{GEN}} = 10 \text{ V},$ $\text{R}_G = 4.5 \Omega, \text{R}_L = 1 \Omega,$ $\text{I}_{\text{DS}} = 50 \text{ A}$	-	39	-	nS
t_r	Turn-on Rise Time		-	122	-	
$\text{t}_{\text{d(off)}}$	Turn-off Delay Time		-	115	-	
t_f	Turn-off Fall Time		-	137	-	
Gate Charge Characteristics ^b						
Q_g	Total Gate Charge	$\text{V}_{\text{DS}} = 50 \text{ V}, \text{V}_{\text{GS}} = 10 \text{ V},$ $\text{I}_{\text{DS}} = 50 \text{ A}$	-	240	-	nC
Q_{gs}	Gate-Source Charge		-	56	-	
Q_{gd}	Gate-Drain Charge		-	60	-	

Notes:

a: Pulse test; Pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$

b: Guaranteed by design, not subject to production testing

7. Typical Characteristics

Figure 1. Maximum Continuous Drain Current vs Case Temperature

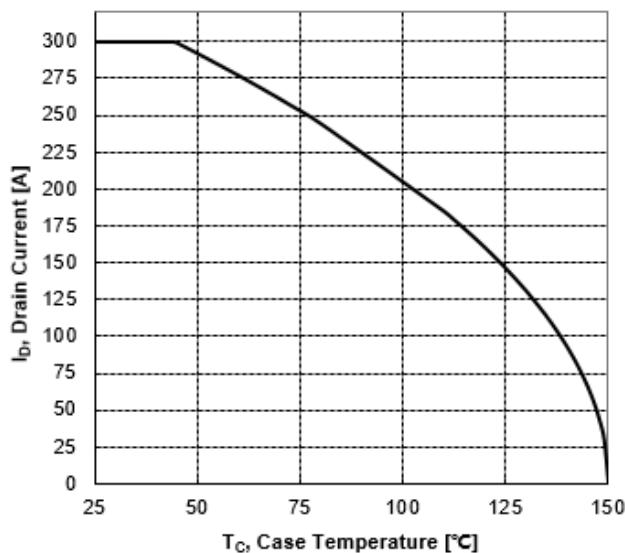


Figure 2. Typical Output Characteristics

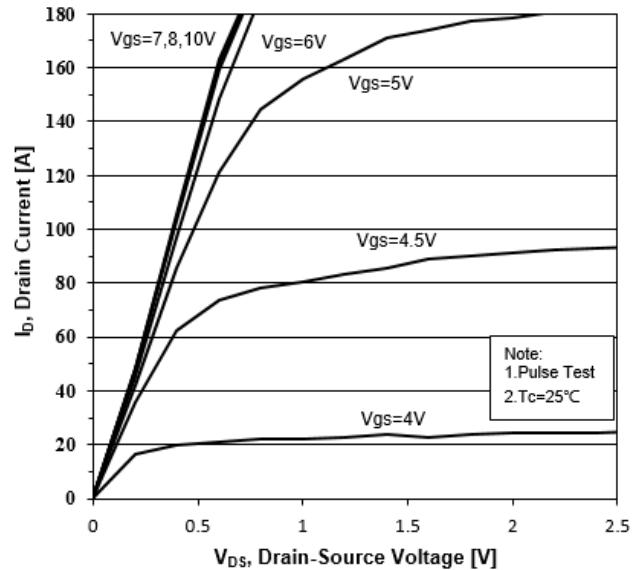


Figure 3. Typical Transfer Characteristics

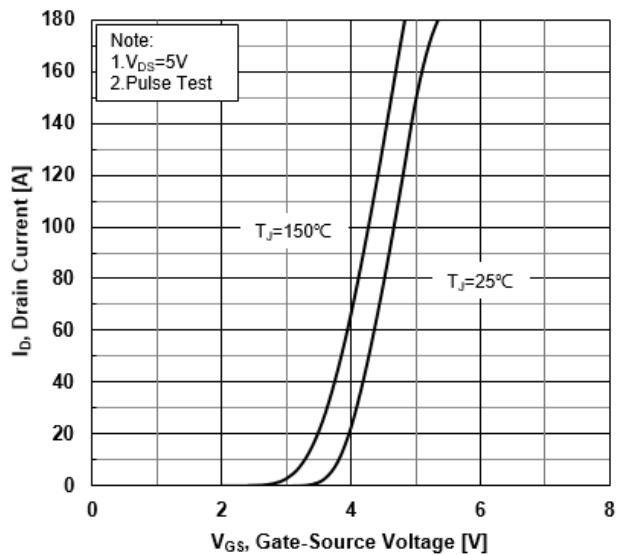
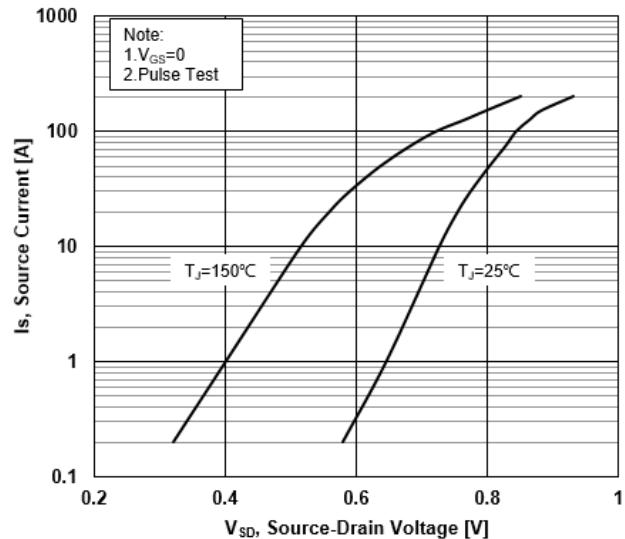


Figure 4. Source-Drain Diode Forward Characteristics



7. Typical Characteristics (cont.)

Figure 5. Drain-Source On-Resistance vs Drain Current

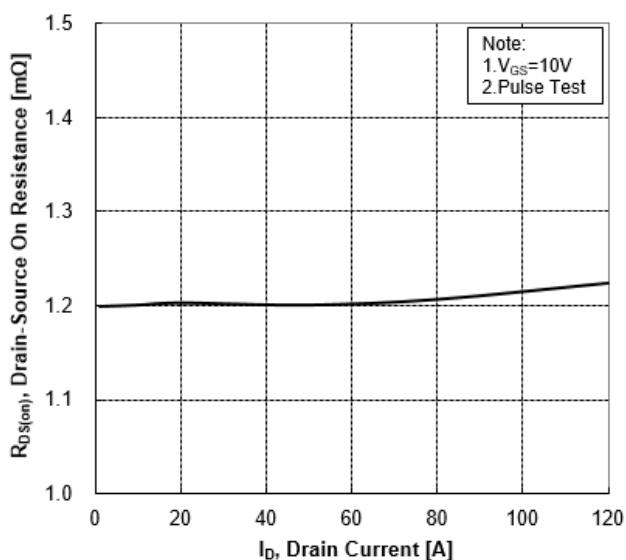


Figure 6. Normalized On-Resistance vs Junction Temperature

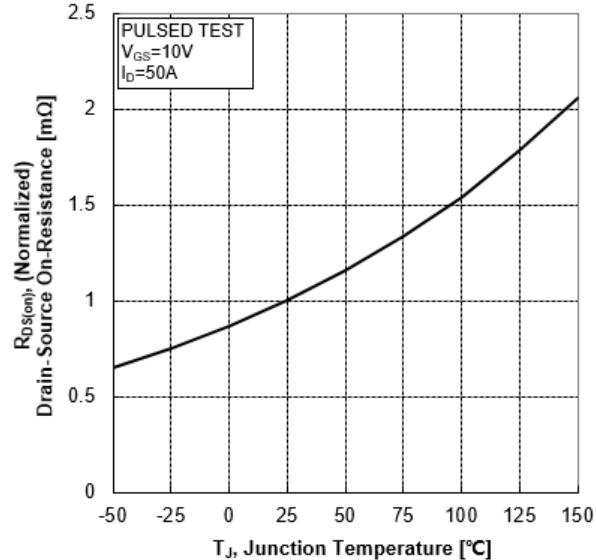


Figure 7. Normalized Threshold Voltage vs Junction Temperature

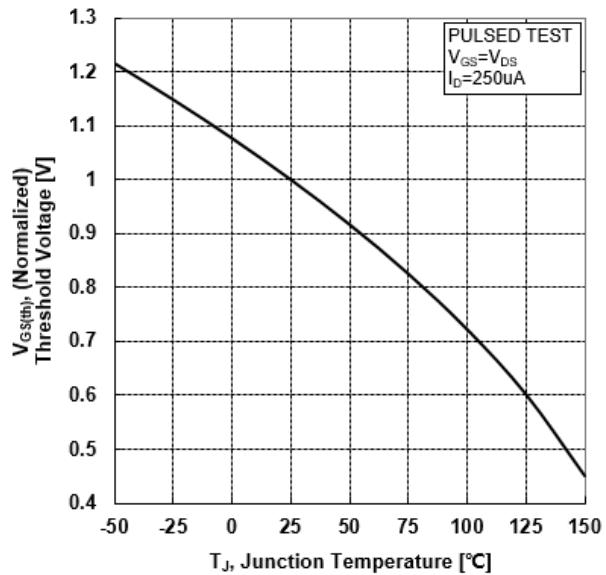
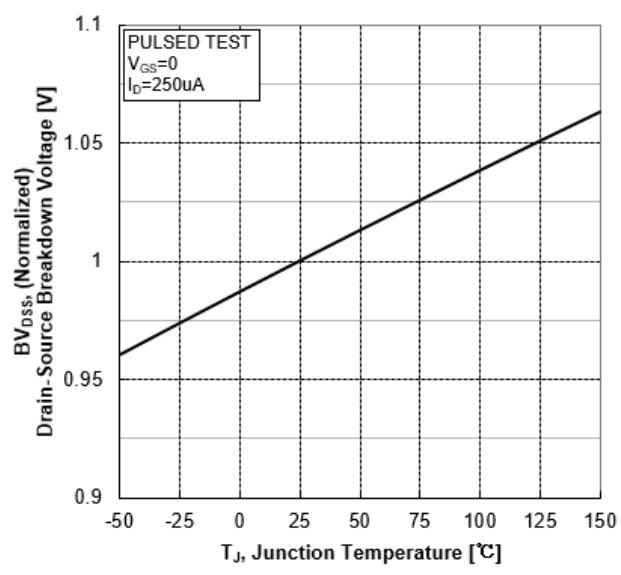
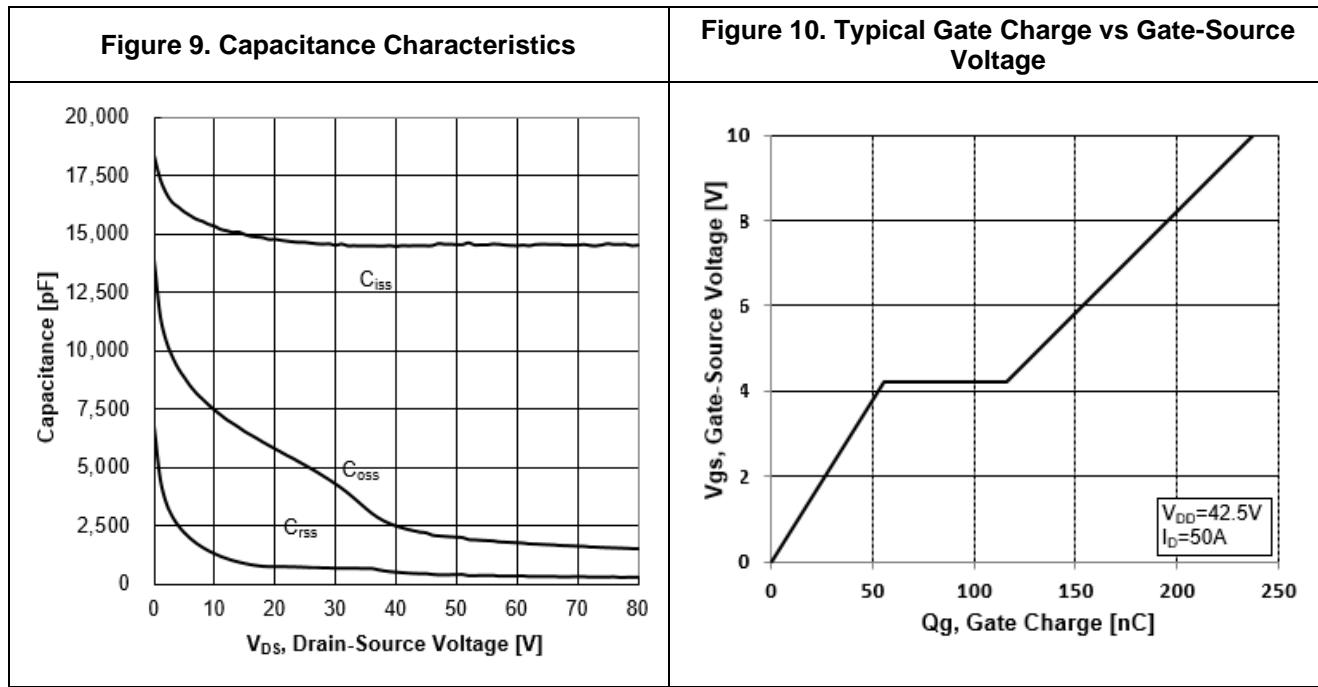


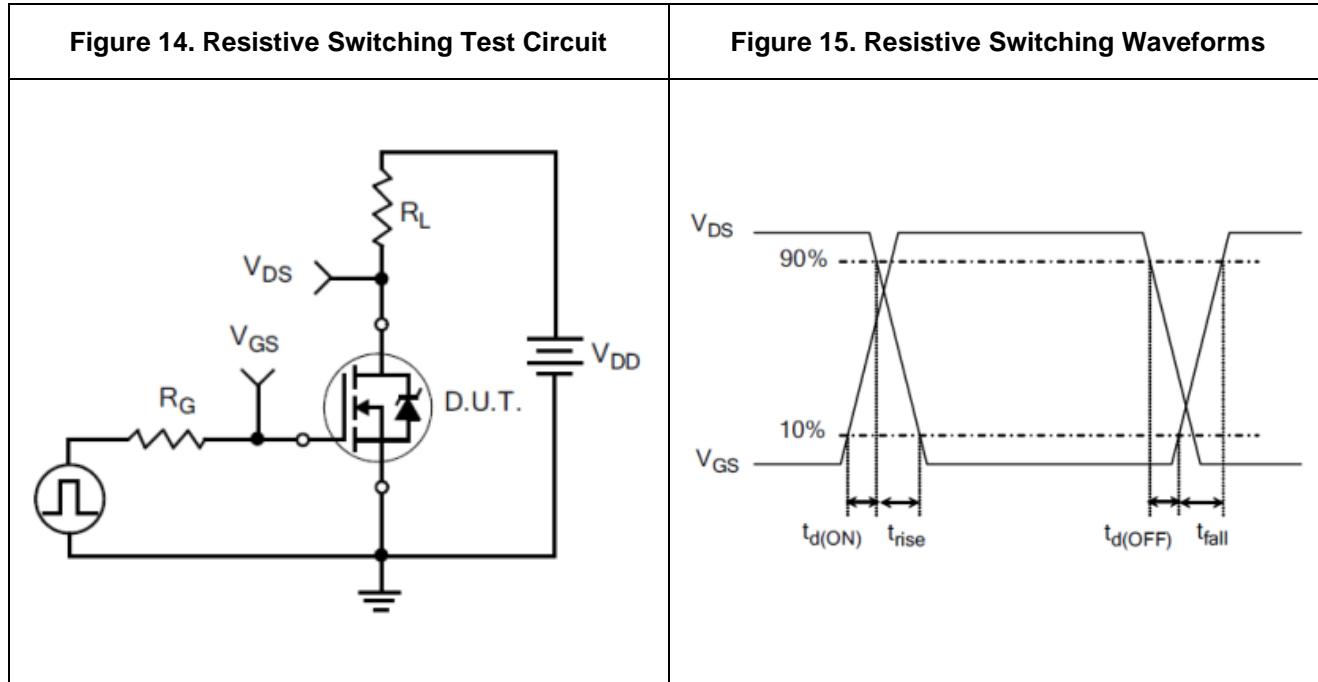
Figure 8. Normalized Breakdown Voltage vs Junction Temperature



7. Typical Characteristics (cont.)



8. Test Circuit and Waveform



8. Test Circuit and Waveform (cont.)

Figure 16. Gate Charge Test Circuit

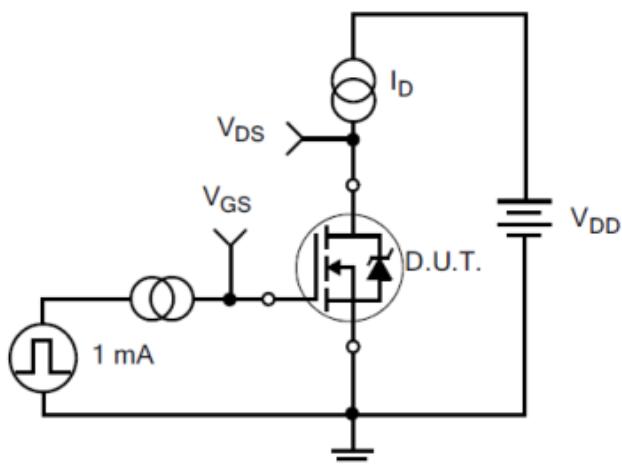


Figure 17. Gate Charge Waveforms

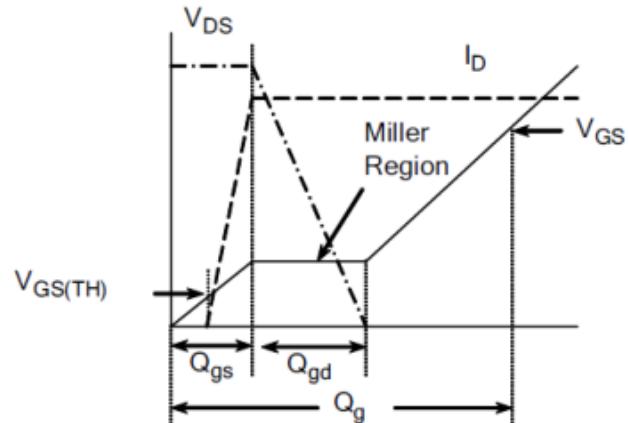


Figure 18. Diode Reverse Recovery Test Circuit

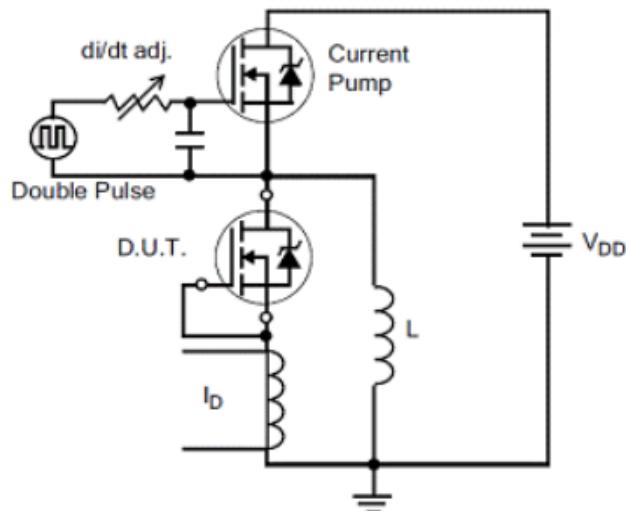
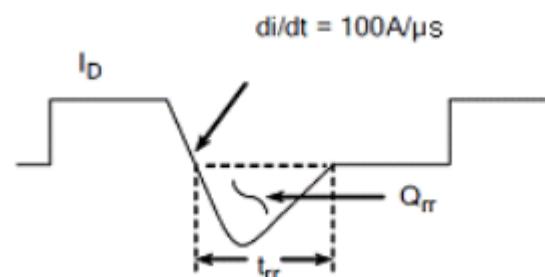


Figure 19. Diode Reverse Recovery Waveform



8. Test Circuit and Waveform (cont.)

Figure 20. Unclamped Inductive Switching Test Circuit

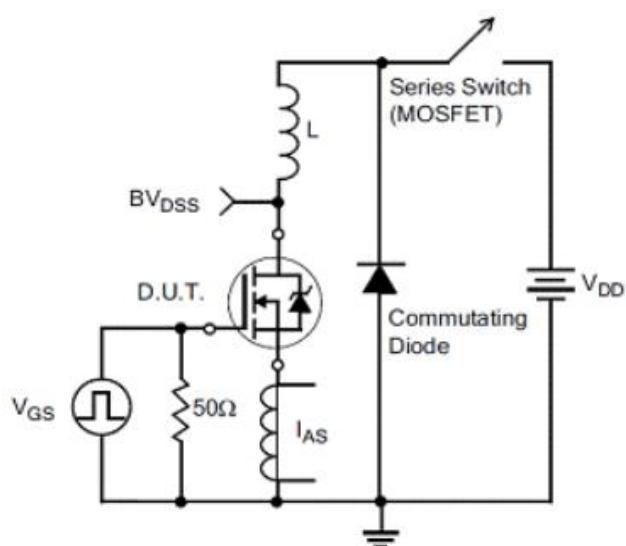
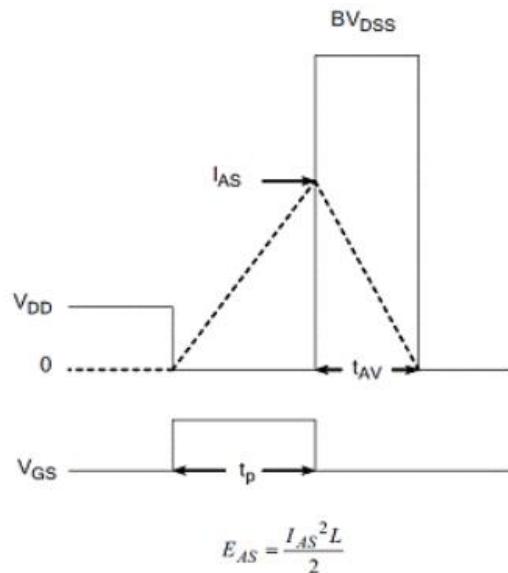
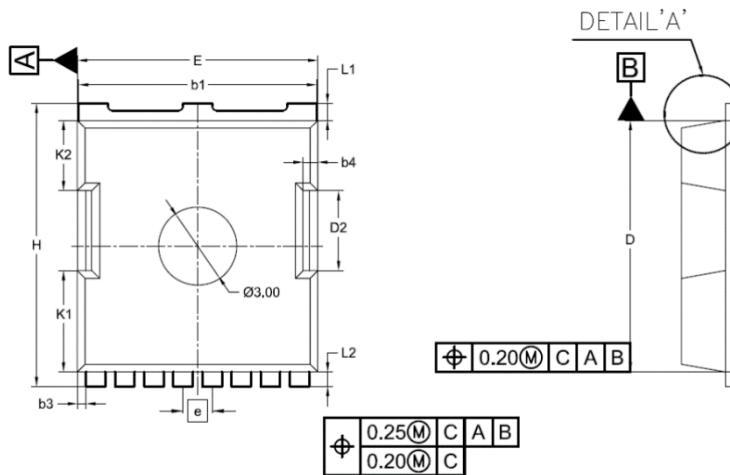


Figure 21. Unclamped Inductive Switching Waveform



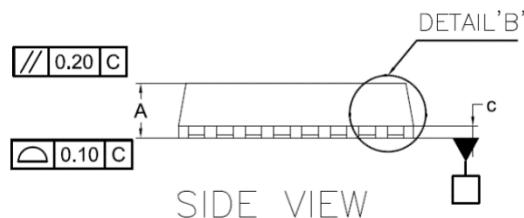
9. Package Dimensions

TOLL-8L Package

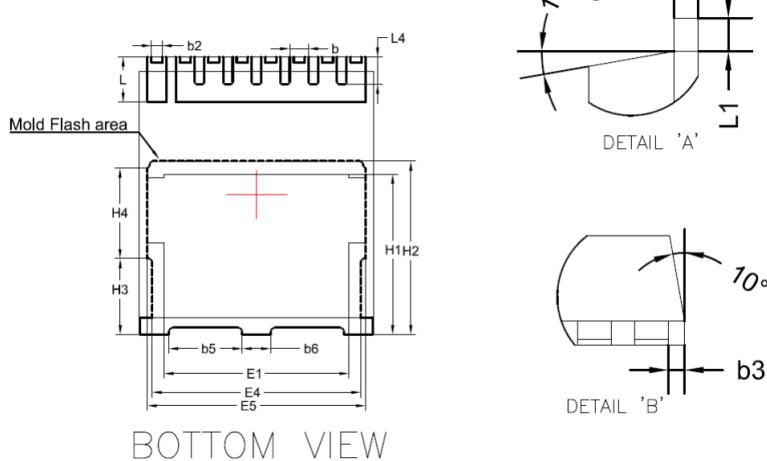


TOP VIEW

SIDE VIEW



SIDE VIEW



BOTTOM VIEW

9. Package Dimensions

TOLL-8L Package

Symbol	Dimensions In Millimeters			Dimensions In Inches		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	2.200	2.300	2.400	0.087	0.091	0.094
c	0.492	0.500	0.508	0.019	0.020	0.021
D	10.280	10.380	10.480	0.405	0.409	0.413
E	9.800	9.900	10.000	0.386	0.390	0.394
e	1.20BSC			0.047BSC		
H	11.580	11.680	11.780	0.456	0.460	0.464
H1	6.650	6.750	6.850	0.262	0.266	0.270
H2	7.300			0.287		
H3	3.200			0.126		
H4	3.800			0.150		
K1	4.180			0.165		
K2	2.900			0.114		
D2	3.300			0.130		
b	0.700	0.800	0.900	0.028	0.031	0.035
b1	9.700	9.800	9.900	0.382	0.386	0.390
b2	0.420	0.460	0.500	0.017	0.018	0.020
b3	0.350			0.014		
b4	0.600			0.024		
b5	3.100			0.122		
b6	1.200			0.047		
L	1.700	1.900	2.100	0.067	0.075	0.083
L1	0.700			0.028		
L2	0.600			0.024		
L4	1.050	1.150	1.250	0.041	0.045	0.049
L5	0.500	0.600	0.700	0.020	0.024	0.028
E1	7.800			0.310		
E4	8.800			0.350		
E5	9.200			0.360		